



enhancement-type p-channel MOSFET designed for . . .

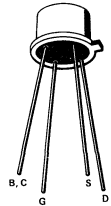
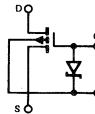
Performance Curves MB
See Section 4

- Audio Amplifiers
- Choppers
- Commutators

ABSOLUTE MAXIMUM RATINGS (25°C)

Drain-to-Source Voltage	-25 V
Gate-to-Source Voltage	-25 V
Gate-to-Drain Voltage	-25 V
Drain Current	-50 mA
Gate Current (Forward Direction For Zener Clamp), ±0.1 mA	
Storage Temperature	-65 to +150°C
Operating Junction Temperature Range	-55 to +125°C
Total Dissipation at 25°C Ambient Temperature (Derate 2.25 mW/°C)	225 mW
Lead Temperature (1/16" from case for 10 seconds)	260°C

TO-72
See Section 5



ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

		Characteristic	Min	Typ	Max	Unit	Test Conditions	
1	S T A T I C	IGSS Gate Leakage Current			-1	nA	VGS = -15 V, VDS = VBS = 0	
2		BVDSS Drain-Source Breakdown Voltage	-25			V	ID = -10 μA, VGS = VBS = 0	
3		VGS(th) Gate Threshold Voltage	-3		-6		VGS = VDS, ID = -10 μA, VBS = 0	
4		ID(off) Drain Cutoff Current			-10	nA	VDS = -20 V, VGS = VBS = 0	
5		ID(on) Drain Current	-3			mA	VGS = VDS = -10 V, VBS = 0	
6		rDS(on) Drain-Source ON Resistance		150		Ω	VGS = -15 V, ID = -1 mA, VBS = 0	
7	D Y N	9fs Common-Source Forward Transconductance	1,000			μmho	VGS = VDS = -10 V, VBS = 0	f = 1 kHz
8			1,000					f = 10 MHz
9		Cgs Gate-Source Capacitance			4		VGS = VDS = -10 V, VBS = 0	f = 1 MHz
10		Cgd Gate-Drain Capacitance			4	pF		
11		Cds Drain-Source Capacitance		0.15				

MB